

ABSTRACT

In a semiconductor device in which first and second transistors are configured so as to have the same electric characteristics as each other, a dummy gate is arranged
5 between the first and second transistors in parallel to gates of the first and second transistors, and arrangement of source and drain regions formed on both sides of the gate of the first transistor, and arrangement of source and drain regions
10 formed on both sides of the gate of the second transistor are the same as each other.